

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	6mΩ @ V <sub>GS</sub> = 10V	80A
	8.5mΩ @ V <sub>GS</sub> = 4.5V	70A

**Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.


**Applications**

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

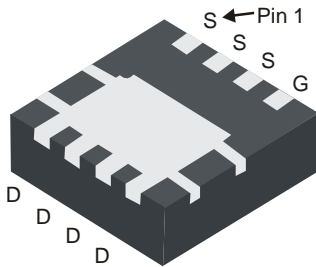
**Features and Benefits**

- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area by enabling smaller end products
- 100% UIS (Avalanche) Rated
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

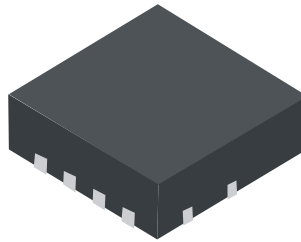
**Mechanical Data**

- Case: POWERDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.008 grams (Approximate)

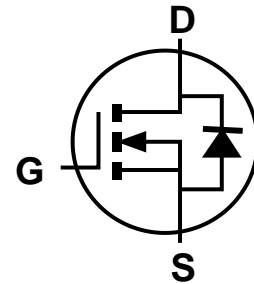
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Bottom View



Top View



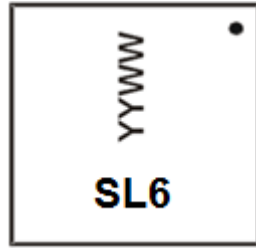
Equivalent Circuit

**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT6007LFG-7	POWERDI <sup>®</sup> 3333-8	2,000/Tape & Reel
DMT6007LFG-13	POWERDI <sup>®</sup> 3333-8	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**

 POWERDI<sup>®</sup>3333-8


SL6 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Digit of Year (ex: 14 = 2014)  
 WW = Week Code (01 ~ 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>A</sub> = +25°C	15
		T <sub>A</sub> = +70°C	12
	I <sub>D</sub>	T <sub>C</sub> = +25°C	80
		T <sub>C</sub> = +70°C	65
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	80	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	80	A
Avalanche Current, L=0.1mH	I <sub>AS</sub>	20	A
Avalanche Energy, L=0.1mH	E <sub>AS</sub>	20	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	55	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	62.5	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. R<sub>θJA</sub> is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.  
 6. Short duration pulse test used to minimize self-heating effect.

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**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 6)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	—	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.5	6	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	6.5	8.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A
Forward Transconductance	G <sub>FS</sub>	—	100	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 7)						
Input Capacitance	C <sub>iss</sub>	—	2090	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	746	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	38.5	—		
Gate Resistance	R <sub>g</sub>	—	0.59	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	19.3	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	41.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	6.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	8.8	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.7	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	4.3	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	23.4	—		
Turn-Off Fall Time	t <sub>F</sub>	—	9.7	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	35.4	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	38.2	—	nC	

Note: 7. Guaranteed by design. Not subject to product testing.

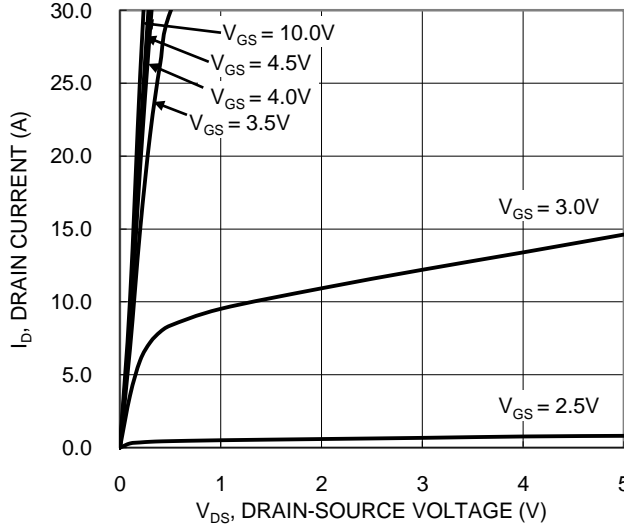


Figure 1. Typical Output Characteristic

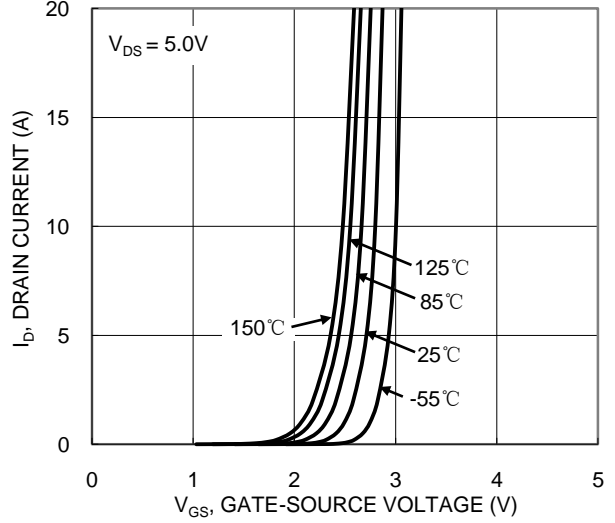


Figure 2. Typical Transfer Characteristic

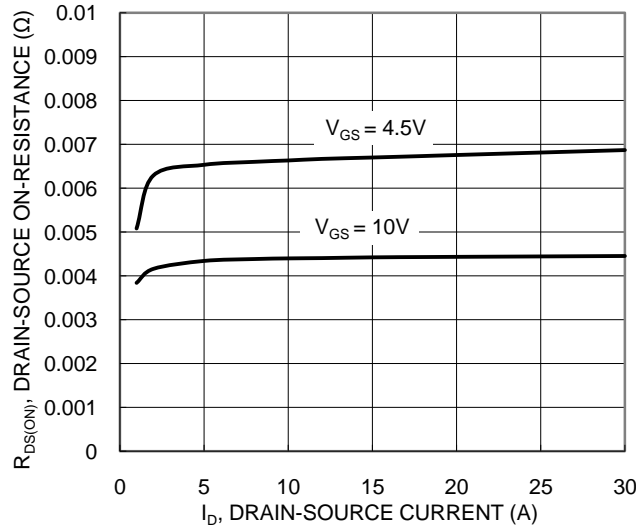


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

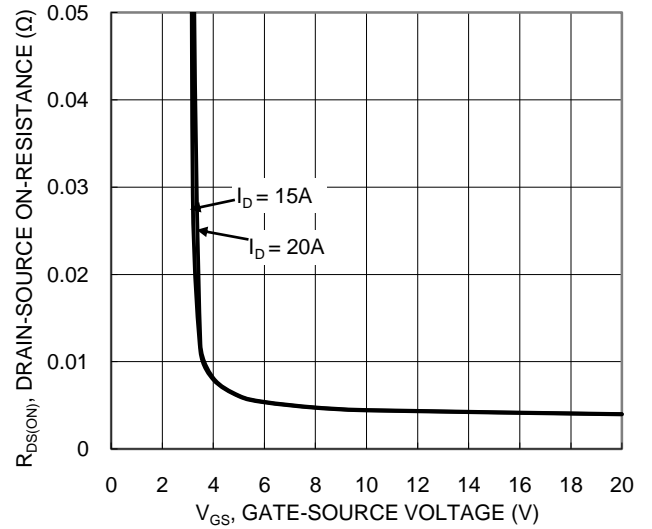


Figure 4. Typical Transfer Characteristic

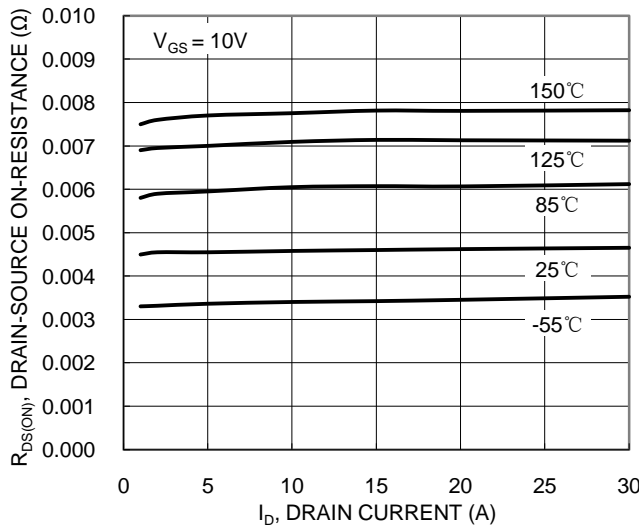


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

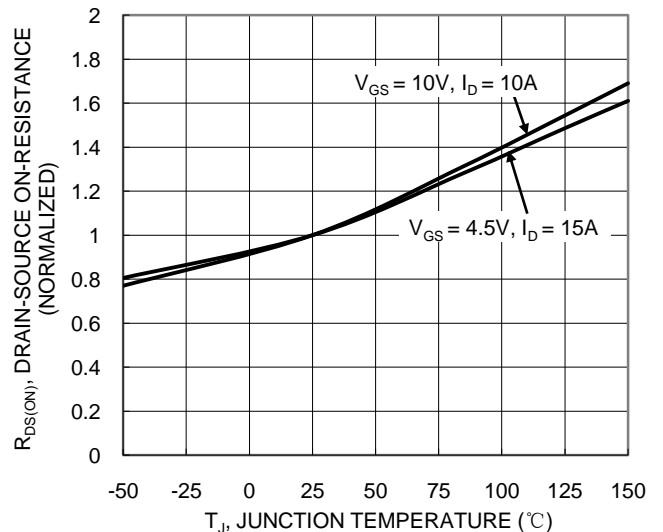


Figure 6. On-Resistance Variation with Temperature

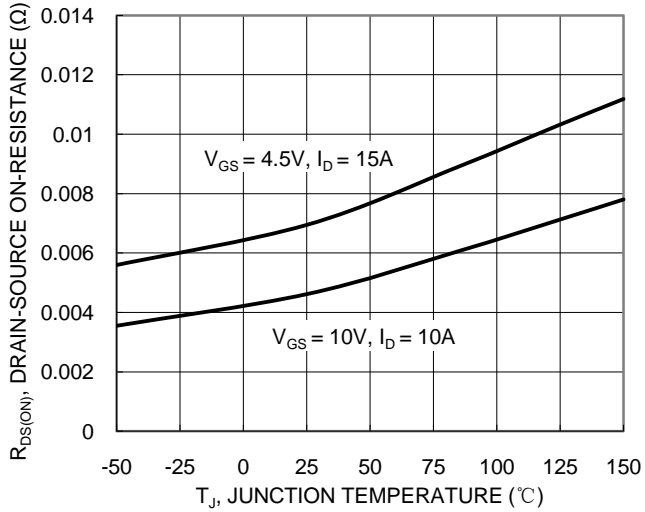


Figure 7. On-Resistance Variation with Temperature

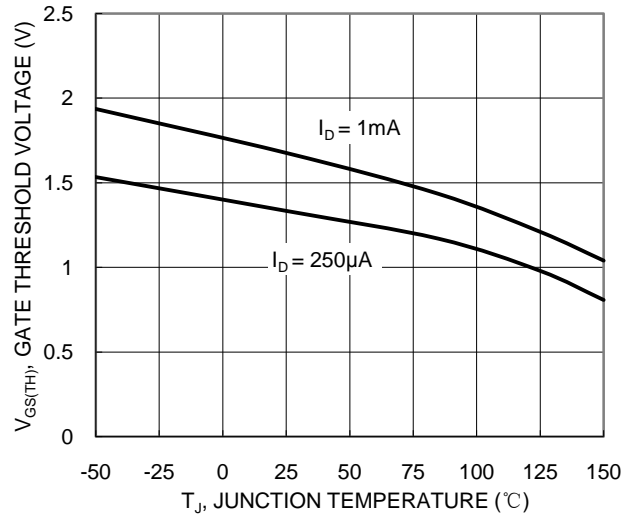


Figure 8. Gate Threshold Variation vs. Junction Temperature

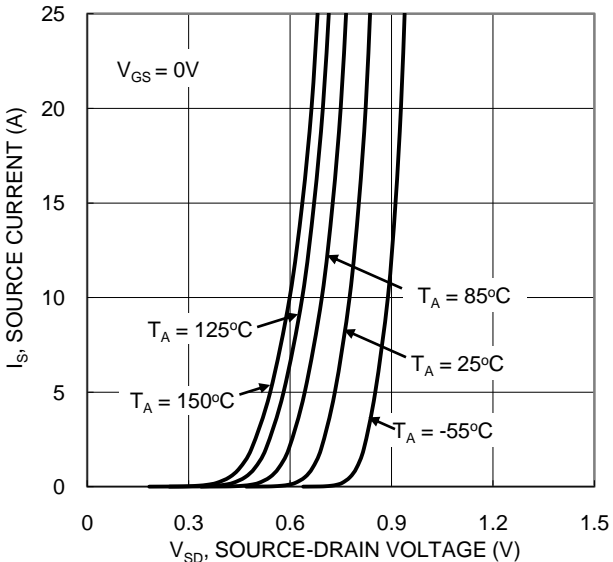


Figure 9. Diode Forward Voltage vs. Current

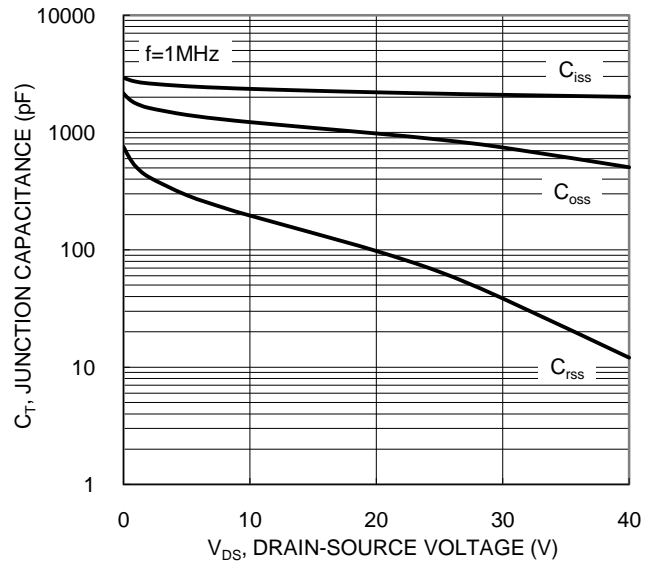


Figure 10. Typical Junction Capacitance

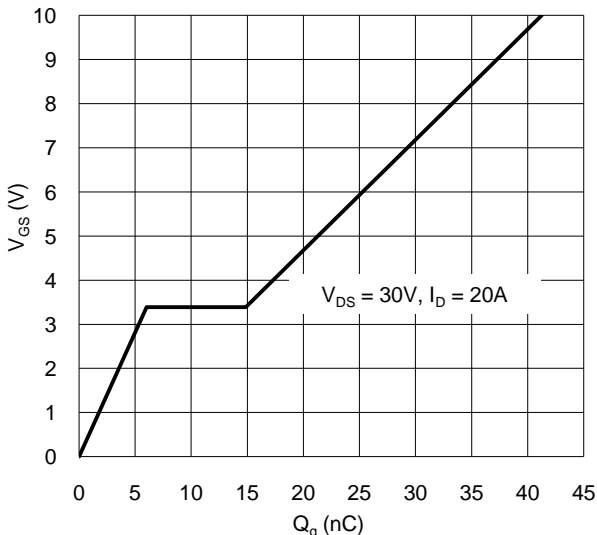


Figure 11. Gate Charge

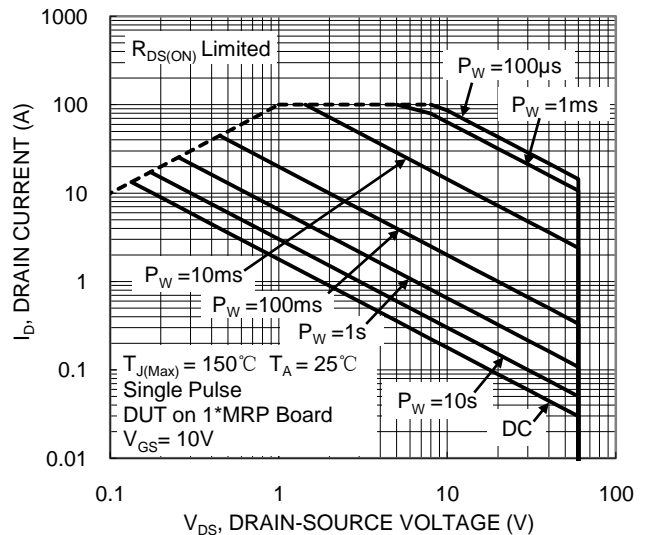


Figure 12. SOA, Safe Operation Area

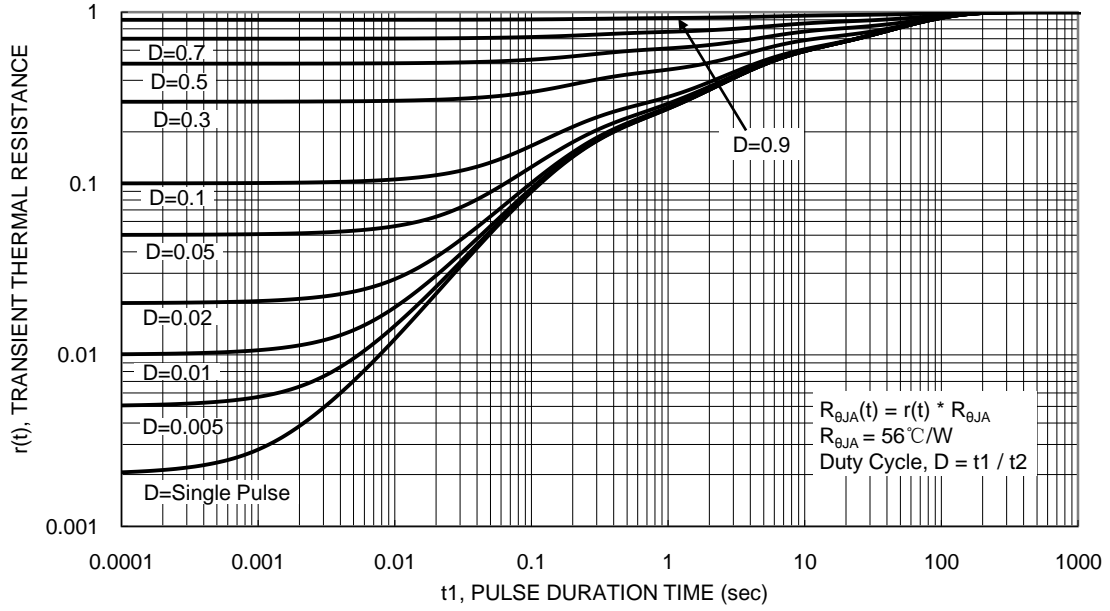
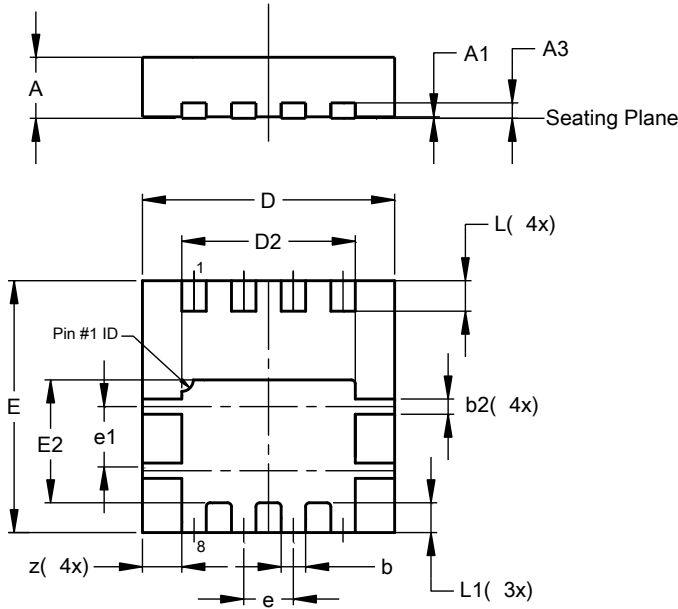


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

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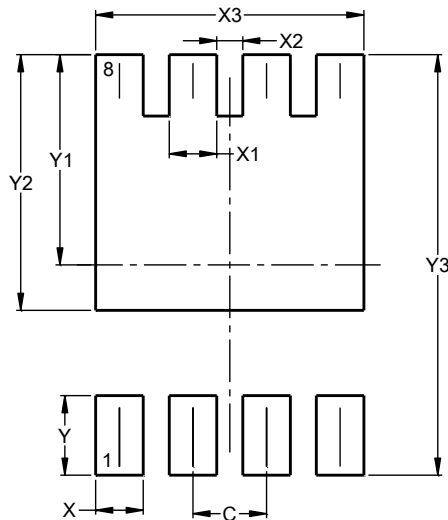
POWERDI <sup>®</sup> 3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	-	-	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

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**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

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Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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